

plane of the drawing. This photoresist mask 9 is used to define n-type channels to be formed in the p-well 8. After the formation of the photoresist mask 9, phosphor ions, indicated by means of dashed lines 11, are implanted in the slice 1. After the removal of the photoresist mask 9, the slice is subjected to a thermal treatment wherein the n-type channel zones 12, shown in Figs. 1 and 6, are formed. Centrally below these channels, the p-well [9] 8 has a smaller thickness. In Fig. 1, the channel regions 12 are shown in a plan view indicated by means of dashed lines.

The paragraph starting on page 4, line 21 has been amended as follows:

After the formation of the n-type channels 12, the gate dielectric 3, 4 is provided, as shown in Fig. 7, with a next photoresist mask 13 comprising strips of photoresist 14 extending transversely to the plane of the drawing. Said photoresist mask [14] 13 serves to define, in the p-well 8, the channel-stop regions separating the n-type channels 12 from each other. After the formation of the photoresist mask 13, boron ions, indicated by means of dashed lines 15, are implanted in the slice 1. After the removal of the photoresist mask 13, the slice is subjected to a thermal treatment wherein the p-type channel-stop regions 16, as shown in Figs. 1 and [7] 8, are formed. The channel-stop regions 16 indicated by means of dashed lines are also shown in a plan view in Fig. 1.

The paragraph starting on page 4, line 32 has been amended as follows:

After the formation of the semiconductor regions 8, 12 and 16, an approximately 500 nm thick n-type conductive layer of polycrystalline silicon [14] is deposited in a customary manner